

FOR IMMEDIATE RELEASE

No. 2401

Product Inquiries

Kazuhiko Sato
High Frequency & Optical Semiconductor
Overseas Marketing Division
Tel: +81-72-780-3835
Sato.Kazuhiko@aj.MitsubishiElectric.co.jp
<http://www.mitsubishichips.com>

Media Contact

Travis Woodward
Public Relations Department
Mitsubishi Electric Corporation
Tel: +81-3-3218-3380
Travis.Woodward@eb.MitsubishiElectric.co.jp
<http://global.mitsubishielectric.com/news/>

**MITSUBISHI ELECTRIC ANNOUNCES SALE OF KU BAND LOW
NOISE GaAs HEMT**

Tokyo, December 14, 2006 – Mitsubishi Electric Corporation (President and CEO: Setsuhiro Shimomura) announced today it has finished development of a Ku band¹ low noise GaAs High Electron Mobility Transistor (HEMT) used in low noise amplifiers for 10-12 GHz Direct Broadcast Satellite (DBS) and Very Small Aperture Terminal (VSAT) reception systems. Sample shipments will begin on February 15, 2007.

¹downlink 12 GHz, uplink 14 GHz

Summary of Sale

Product name	Model	Summary	Price of Sample (exl. Tax)	Sample shipment date	Production
Low noise GaAs HEMT	MGF4941AL	NF : 0.35dB Gs : 13.5dB (f=12GHz)	40yen	02/15/2007	4 million /month

Aim of Sale

Satellites that use wireless communication systems can build a much larger service area network compared to fiber optic cable communication systems, etc. It is expected to be quickly adopted by countries experiencing economic high-speed growth and developing communication infrastructure, in particular China, which has launched its first communications satellite in October of this year with a second satellite launch planned for 2007, and is expected to greatly increase demand in preparation for the 2008 Olympics in Beijing.

The HEMT we have developed is a transistor used in first stage low-noise amplifiers for down converters in receiver systems that convert 12 GHz band electrical waves sent from broadcast and/or communications satellites into intermediate frequencies in the 1-2 GHz band. In addition to using the industry-standard Micro X Type²⁶ in the package for easy mounting to a substrate, the device has enhanced noise characteristics

which contribute to the improved productivity and functionality of satellite communications equipment.

²generic term for a small package with 4 leads shaped in a cross

Product Features

1. Micro X standard package

Using the micro X type standard for the package, it is easier to mount it to the motherboard, improving satellite communication device productivity. Adding the previous small footprint leadless type, customers can choose between two types to meet their needs.

2. 0.05dB improved noise factor

An improved surface treatment process improves noise factor, a measurement of feedback emitted from a device, by 0.05dB³ compared to previous models⁴ to 0.35dB

³standard value 12 GHz frequency

⁴compared to our MGF4953A

Future Developments

We plan to produce plastic package HEMT for Ka band (18-20 GHz) DBS

About Mitsubishi Electric

With over 80 years of experience in providing reliable, high-quality products to both corporate clients and general consumers all over the world, Mitsubishi Electric Corporation (TSE:6503) is a recognized world leader in the manufacture, marketing and sales of electrical and electronic equipment used in information processing and communications, space development and satellite communications, consumer electronics, industrial technology, energy, transportation and building equipment. The company recorded consolidated group sales of 3,604 billion yen (US\$ 30.8billion*) in the fiscal year ended March 31, 2006. For more information visit <http://global.mitsubishielectric.com>

*At an exchange rate of 117 yen to the US dollar, the rate given by the Tokyo Foreign Exchange Market on March 31, 2006.

###